

# FDP032N08

## N-Channel PowerTrench® MOSFET

75V, 235A, 3.2mΩ

### Features

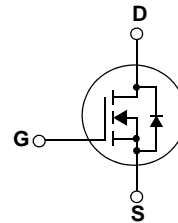
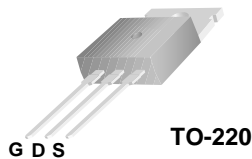
- $R_{DS(on)} = 2.5m\Omega$  (Typ.) @  $V_{GS} = 10V, I_D = 75A$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low  $R_{DS(on)}$
- High power and current handling capability
- RoHS compliant

### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### Application

- DC to DC converters / Synchronous Rectification



### MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted\*

Symbol	Parameter	FDP032N08	Units
$V_{DSS}$	Drain to Source Voltage	75	V
$V_{GSS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ C$ , Silicon Limited)	235*
		- Continuous ( $T_C = 100^\circ C$ , Silicon Limited)	165*
		- Continuous ( $T_C = 25^\circ C$ , Package Limited)	120
$I_{DM}$	Drain Current - Pulsed (Note 1)	940	A
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1995	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ C$ )		375
		- Derate above $25^\circ C$	2.5
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

\*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

### Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.4	$^\circ C/W$
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

**Package Marking and Ordering Information**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP032N08	FDP032N08	TO-220	-	-	50

**Electrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}, T_C = 25^\circ\text{C}$	75	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.05	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 75\text{V}, V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 75\text{V}, T_C = 150^\circ\text{C}$	-	-	500	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 75\text{A}$	-	2.5	3.2	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 75\text{A}$ (Note 4)	-	180	-	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	11400	15160	pF
$C_{oss}$	Output Capacitance		-	1360	1810	pF
$C_{rss}$	Reverse Transfer Capacitance		-	595	800	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 60\text{V}, I_D = 75\text{A}$ $V_{GS} = 10\text{V}$ (Note 4, 5)	-	169	220	nC
$Q_{gs}$	Gate to Source Gate Charge		-	60	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	47	-	nC

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 37.5\text{V}, I_D = 75\text{A}$ $R_{GEN} = 25\Omega, V_{GS} = 10\text{V}$ (Note 4, 5)	-	230	470	ns
$t_r$	Turn-On Rise Time		-	191	392	ns
$t_{d(off)}$	Turn-Off Delay Time		-	335	680	ns
$t_f$	Turn-Off Fall Time		-	121	252	ns

**Drain-Source Diode Characteristics**

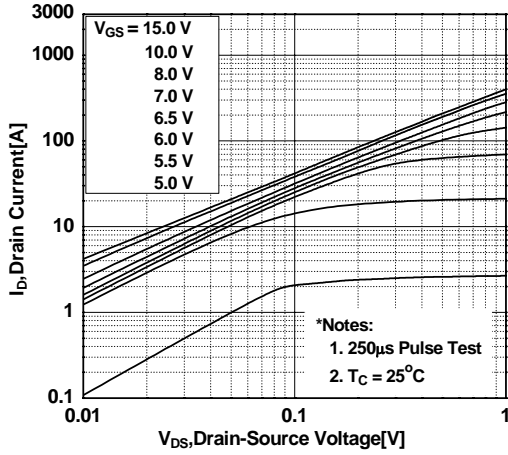
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	235	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	940	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 75\text{A}$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_{SD} = 75\text{A}$	-	53	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	77	-	nC

**Notes:**

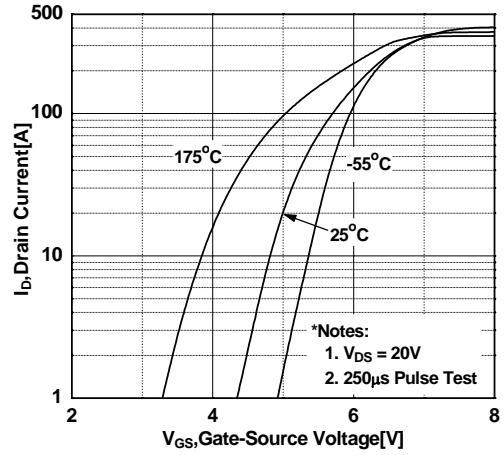
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 0.71\text{mH}, I_{AS} = 75\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 75\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

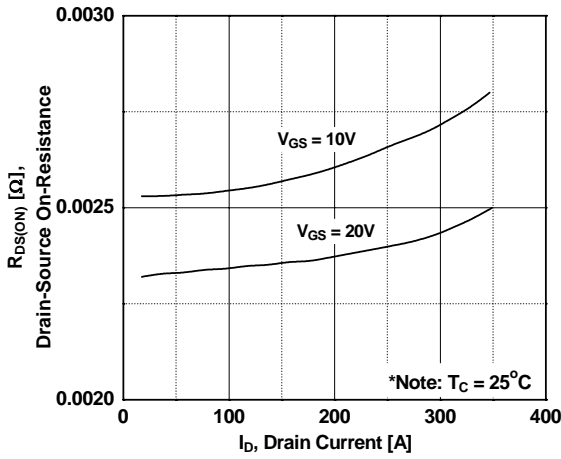
**Figure 1. On-Region Characteristics**



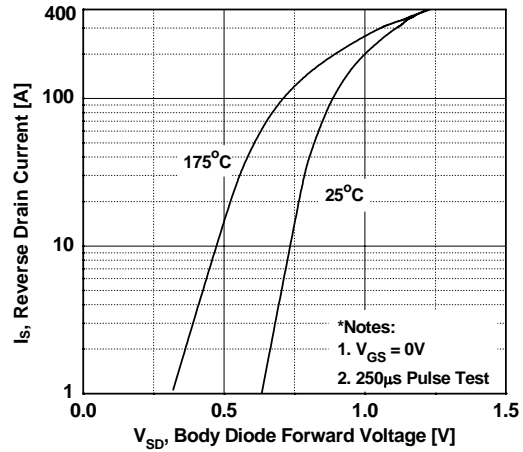
**Figure 2. Transfer Characteristics**



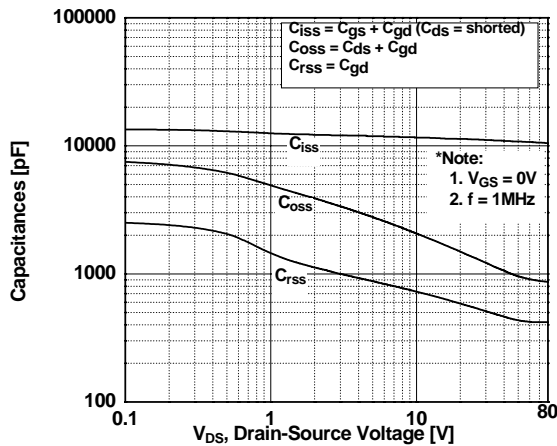
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



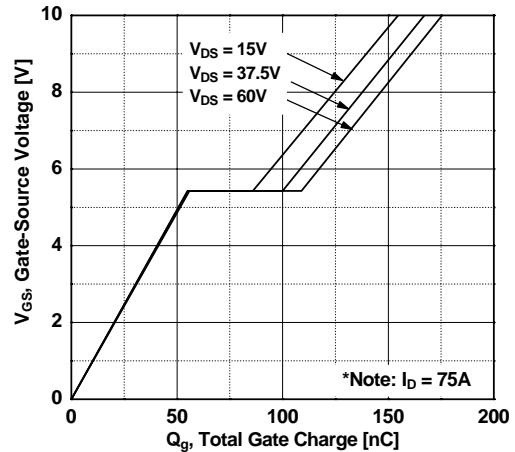
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

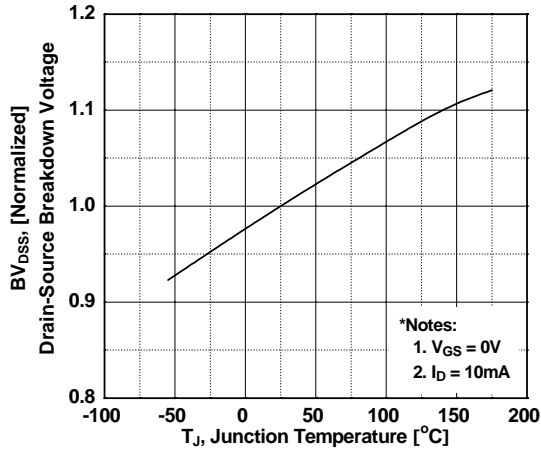


Figure 8. On-Resistance Variation vs. Temperature

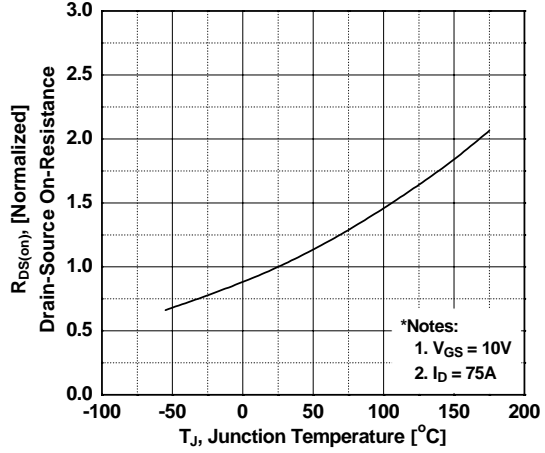


Figure 9. Maximum Safe Operating Area

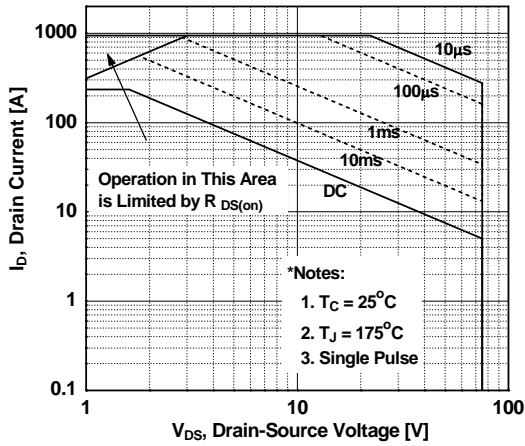


Figure 10. Maximum Drain Current vs. Case Temperature

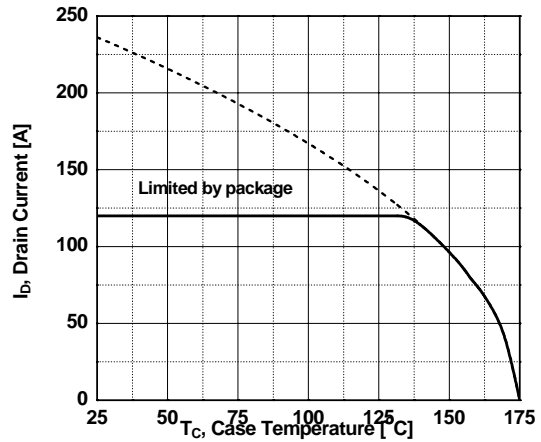
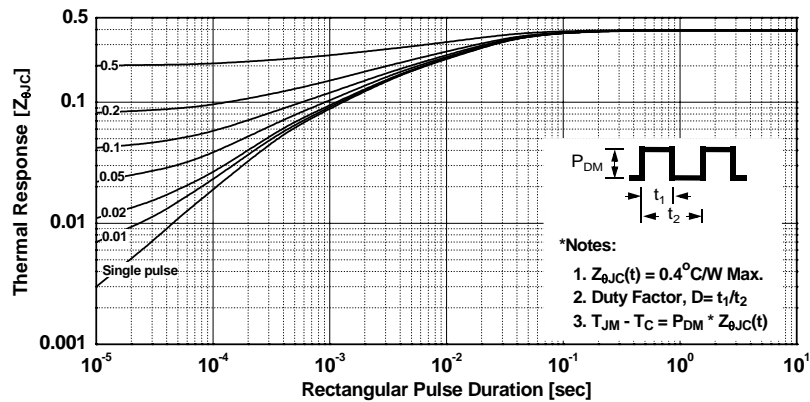
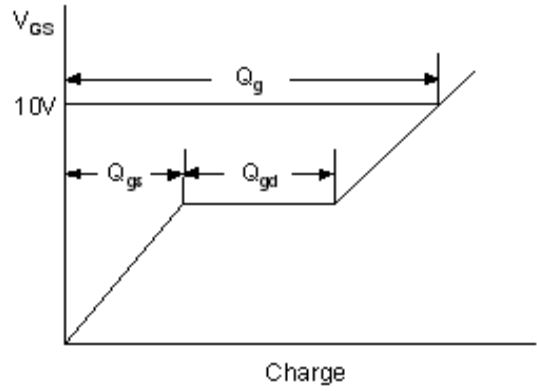
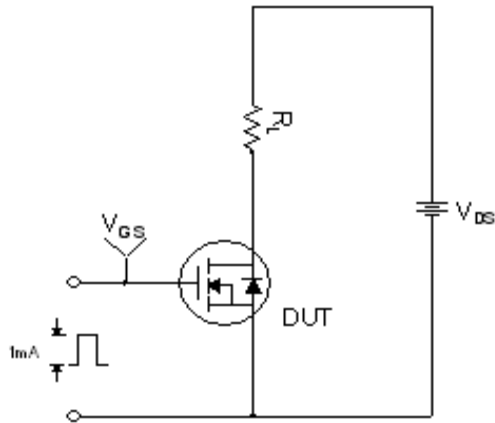


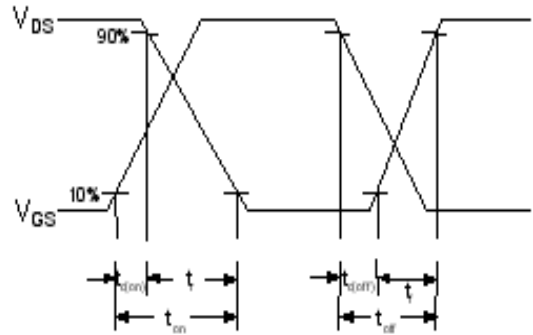
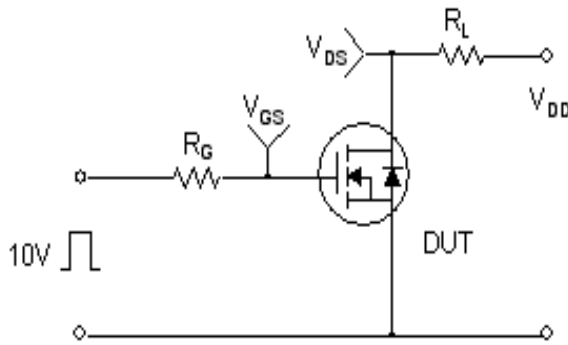
Figure 11. Transient Thermal Response Curve



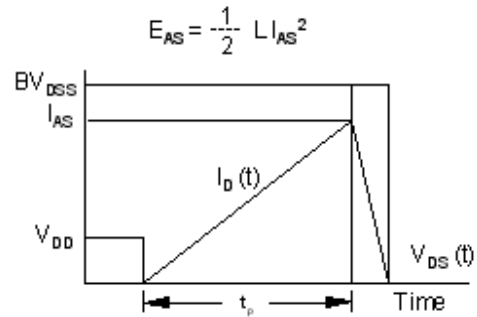
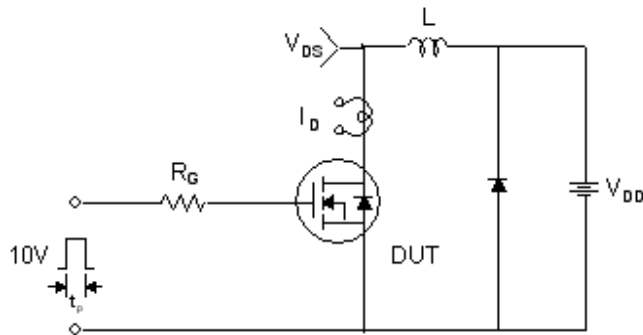
**Gate Charge Test Circuit & Waveform**



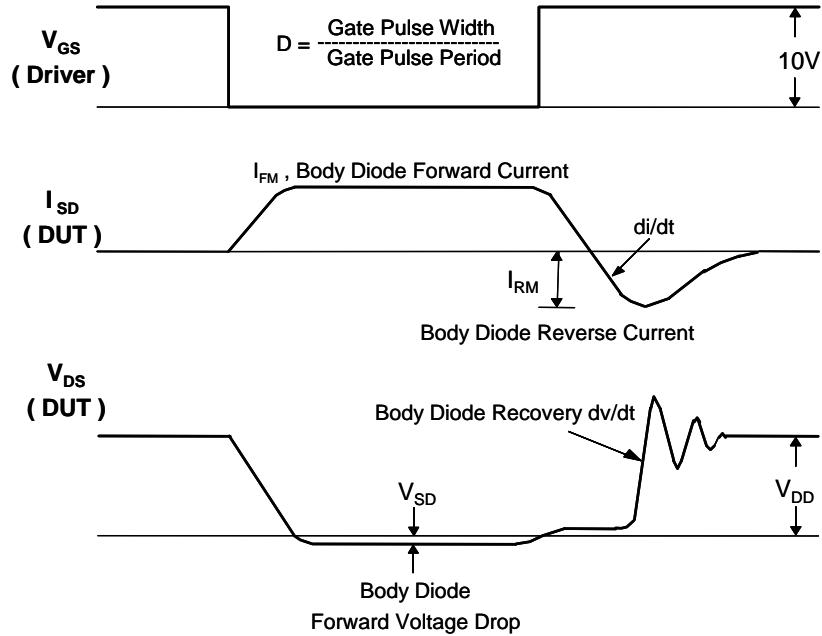
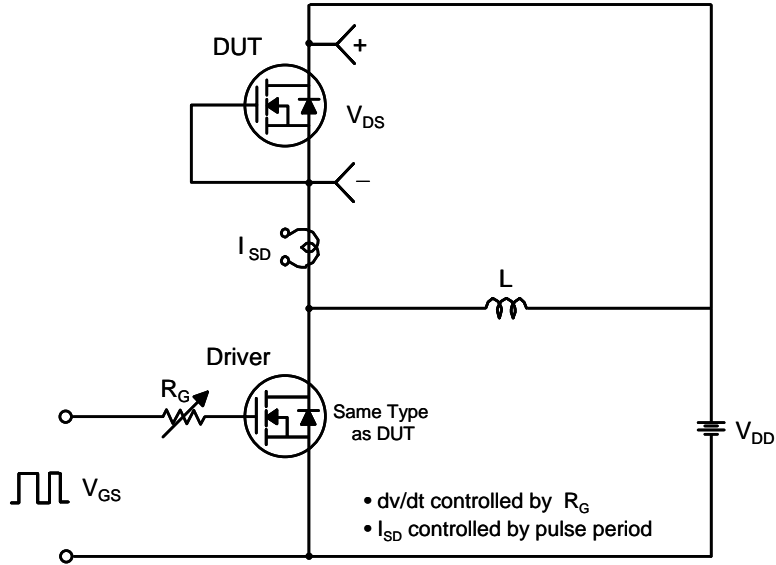
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

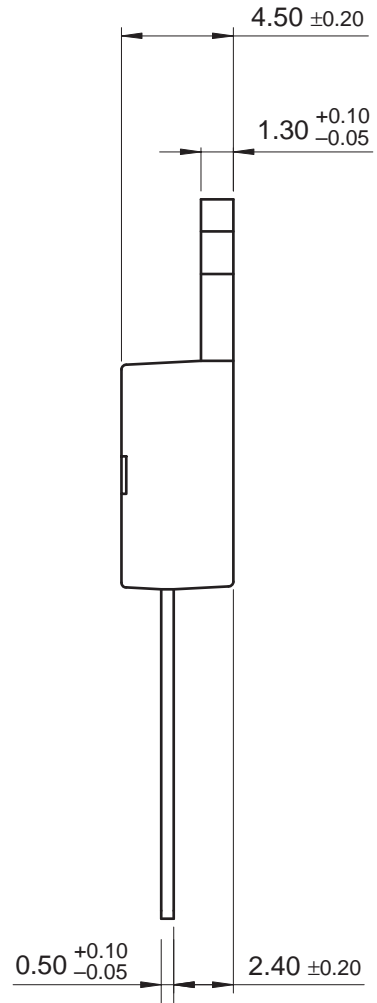
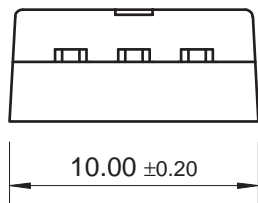
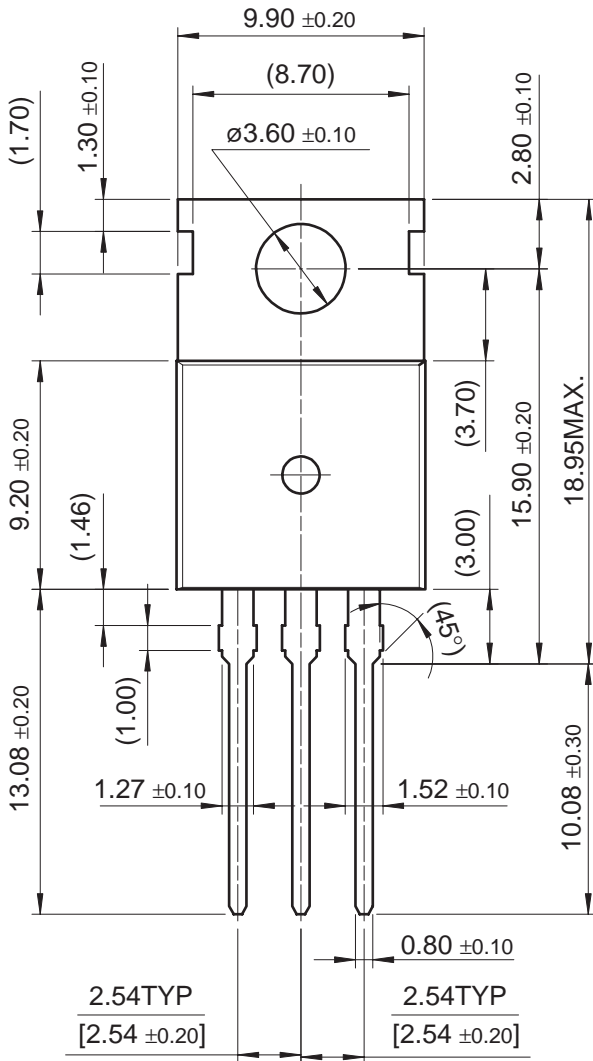


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Mechanical Dimensions

## TO-220





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